



9018

NPN SILICON TRANSISTOR

FEATURES

Power dissipation

$$P_{CM} : 0.31 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

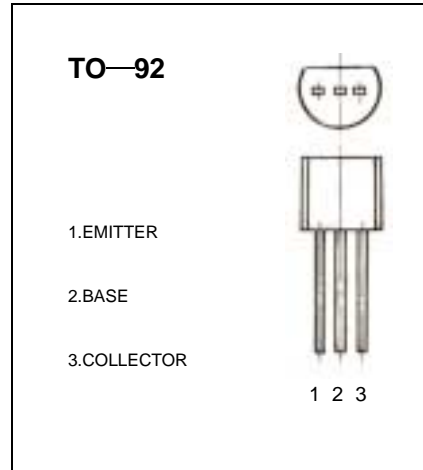
$$I_{CM} : 0.05 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : 25 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu\text{A}, I_E = 0$	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.1 \text{ mA}, I_B = 0$	18			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu\text{A}, I_C = 0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 15 \text{ V}, I_B = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3 \text{ V}, I_C = 0$			0.1	μA
DC current gain	$H_{FE(1)}$	$V_{CE} = 5 \text{ V}, I_C = 1 \text{ mA}$	28		270	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$			1.4	V
Transition frequency	f_T	$V_{CE} = 5 \text{ V}, I_C = 5 \text{ mA}$ $f = 400 \text{ MHz}$	600			MHz

CLASSIFICATION OF $H_{FE(1)}$

Rank	D	E	F	G	H	I	J
Range	28-45	39-60	54-80	72-108	97-146	132-198	180-270